



STD8NM60ND, STF8NM60ND STP8NM60ND, STU8NM60ND

N-channel 600 V, 0.59 Ω , 7 A, FDmesh™ II Power MOSFET
TO-220, TO-220FP, IPAK, DPAK

Features

Type	V _{DSS} (@T _{jmax})	R _{DS(on)} max	I _D
STD8NM60ND	650 V	< 0.70 Ω	7 A
STF8NM60ND	650 V	< 0.70 Ω	7 A
STP8NM60ND	650 V	< 0.70 Ω	7 A ⁽¹⁾
STU8NM60ND	650 V	< 0.70 Ω	7 A

1. Limited only by maximum temperature allowed

- The worldwide best R_{DS(on)}* area amongst the fast recovery diode devices
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- Extremely high dv/dt and avalanche capabilities

Application

- Switching applications

Description

The FDmesh™ II series belongs to the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a new vertical structure to the company's strip layout and associates all advantages of reduced on-resistance and fast switching with an intrinsic fast-recovery body diode. Strongly recommended for bridge topologies, in ZVS phase-shift converters.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STD8NM60ND	8NM60ND	DPAK	Tape and reel
STF8NM60ND	8NM60ND	TO-220FP	Tube
STP8NM60ND	8NM60ND	TO-220	Tube
STU8NM60ND	8NM60ND	IPAK	Tube

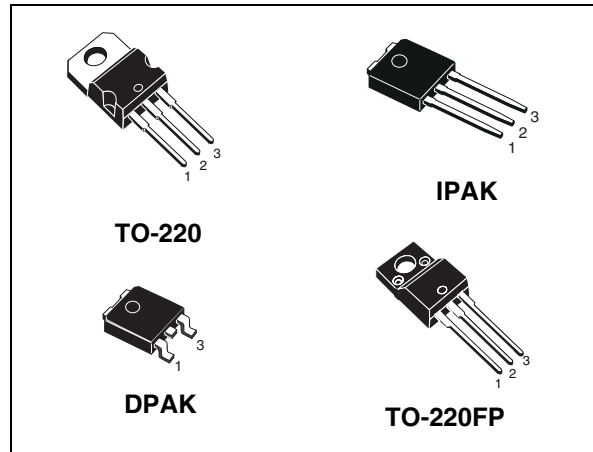
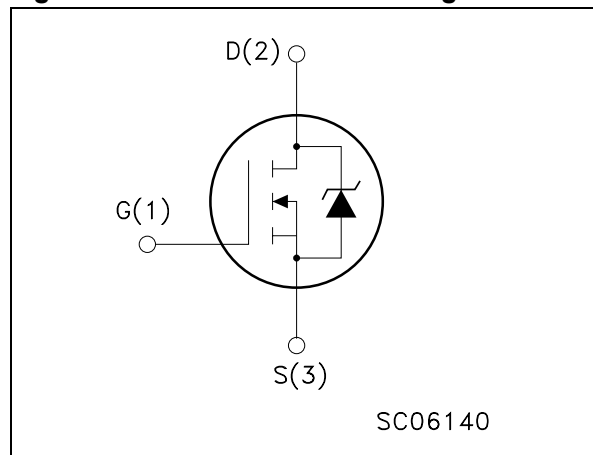


Figure 1. Internal schematic diagram



Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics	6
3	Test circuits	9
4	Package mechanical data	10
5	Packaging mechanical data	15
6	Revision history	16

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value				Unit
		TO-220	DPAK	IPAK	TO-220FP	
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	600				V
V_{GS}	Gate-source voltage	± 30				V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	7		7 ⁽¹⁾		A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	4.4		4.4 ⁽¹⁾		A
I_{DM} ⁽²⁾	Drain current (pulsed)	28		28 ⁽¹⁾		A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	70		25		W
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t = 1\text{ s}; T_C = 25\text{ }^\circ\text{C}$)	2500				V
dv/dt ⁽³⁾	Peak diode recovery voltage slope	40				V/ns
T_{stg}	Storage temperature	-55 to 150				$^\circ\text{C}$
T_j	Max. operating junction temperature	150				$^\circ\text{C}$

- Limited only by maximum temperature allowed
- Pulse width limited by safe operating area
- $I_{SD} \leq 7\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DD} = 80\% V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value				Unit
		TO-220	DPAK	IPAK	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case	1.79			5	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-amb	62.5		100	62.5	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb		50			$^\circ\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300				$^\circ\text{C}$

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	2.5	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AS}$, $V_{DD} = 50\text{ V}$)	200	mJ

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0$	600			V
$dv/dt^{(1)}$	Drain-source voltage slope	$V_{DD} = 480\text{ V}$, $I_D = 7\text{ A}$, $V_{GS} = 10\text{ V}$		45		V/ns
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$, $V_{DS} = \text{Max rating}$, $T_c = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 3.5\text{ A}$		0.59	0.70	Ω

1. Characteristics value at turn off on inductive load

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{ V}$, $I_D = 5\text{ A}$		7.5		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 50\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$		560 37 4		pF pF pF
$C_{oss\text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0$, $V_{DS} = 0\text{ to }480\text{ V}$		90		pF
R_G	Gate input resistance	$f = 1\text{ MHz}$ Gate DC Bias = 0 Test Signal Level = 20 mV Open Drain		6		Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 480\text{ V}$, $I_D = 7\text{ A}$ $V_{GS} = 10\text{ V}$ <i>Figure 19</i>		22 4 13		nC nC nC

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$, $I_D = 7\text{ A}$,		9		ns
t_r	Rise time	$R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$		22		ns
$t_{d(off)}$	Turn-off delay time	Figure 18 ,		37		ns
t_f	Fall time	Figure 23		22		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				7	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				28	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 7\text{ A}$, $V_{GS} = 0$			1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 7\text{ A}$, $di/dt = 100$		120		ns
Q_{rr}	Reverse recovery charge	$A/\mu s$, $V_{DD} = 30\text{ V}$,		0.49		μC
I_{RRM}	Reverse recovery current	Figure 20		8		A
t_{rr}	Reverse recovery time	$I_{SD} = 7\text{ A}$,		170		ns
Q_{rr}	Reverse recovery charge	$di/dt = 100\text{ A}/\mu s$,		0.75		μC
I_{RRM}	Reverse recovery current	$V_{DD} = 30\text{ V}$, $T_j = 150^\circ C$		9		A
		Figure 20				

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics

Figure 2. Safe operating area for TO-220

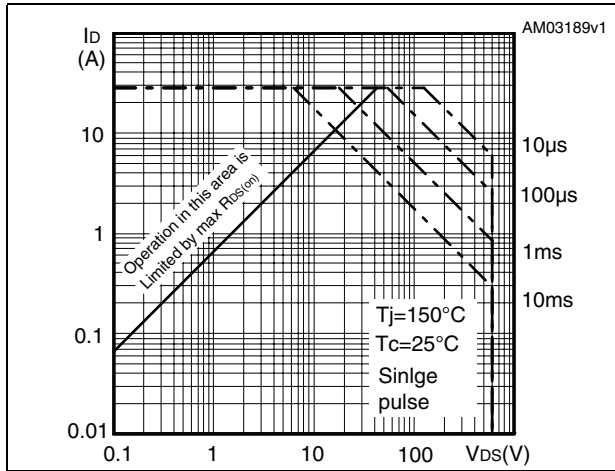


Figure 3. Thermal impedance for TO-220

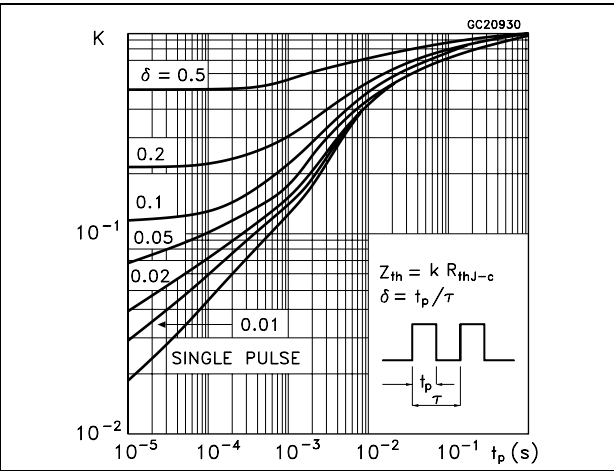


Figure 4. Safe operating area for DPAK, IPAK

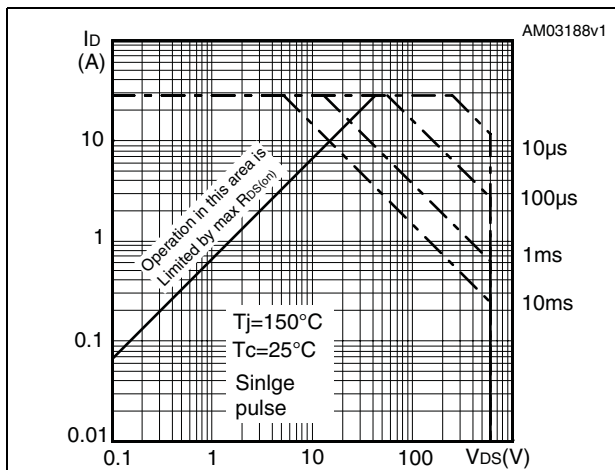


Figure 5. Thermal impedance for DPAK, IPAK

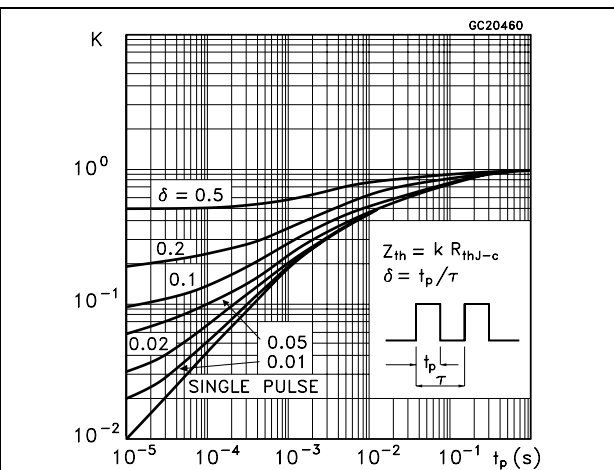


Figure 6. Safe operating area for TO-220FP

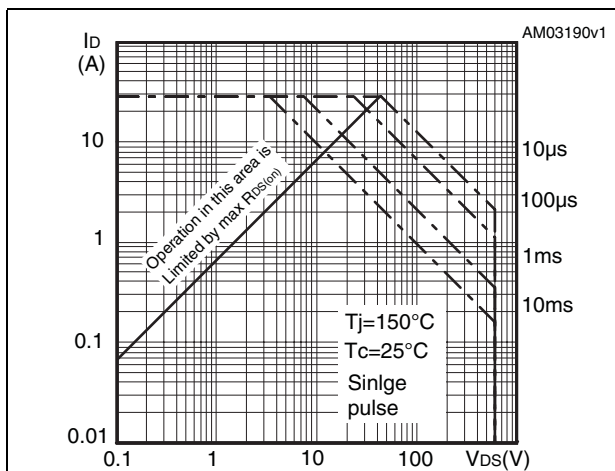


Figure 7. Thermal impedance for TO-220FP

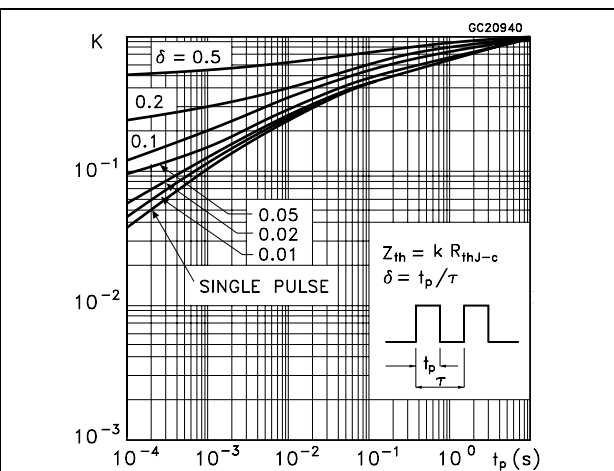


Figure 8. Output characteristics

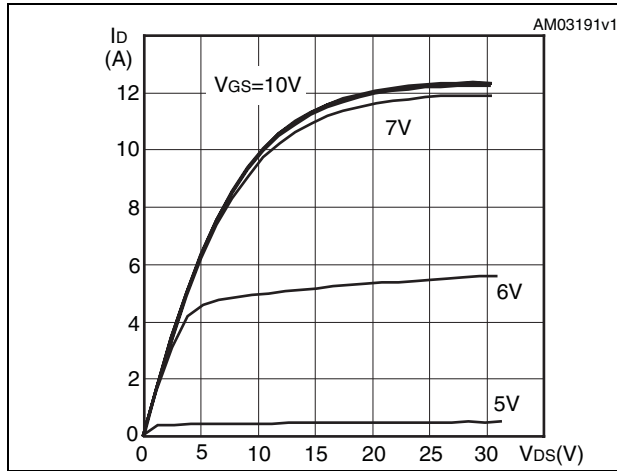


Figure 9. Transfer characteristics

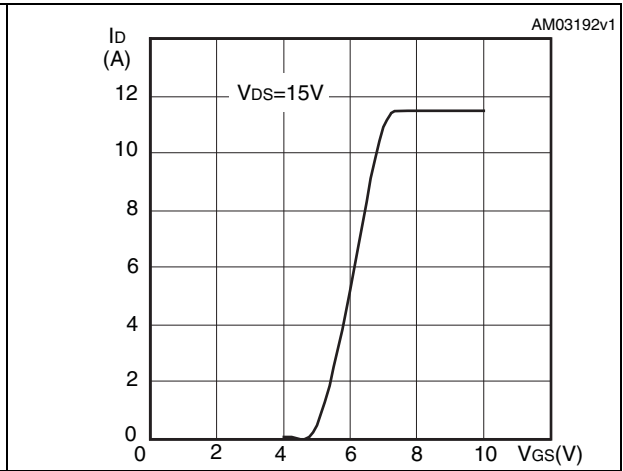


Figure 10. Transconductance

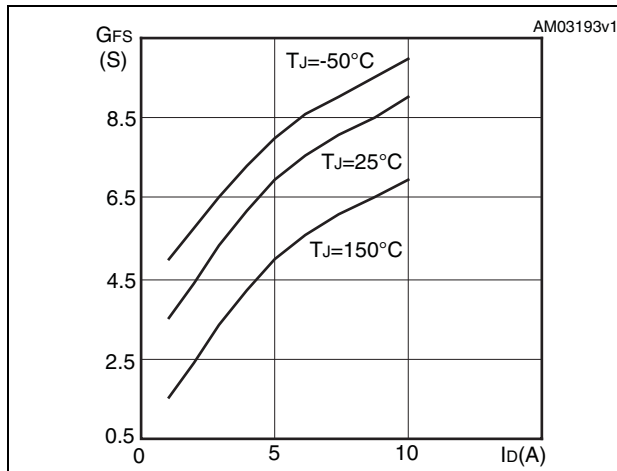


Figure 11. Static-drain source on resistance

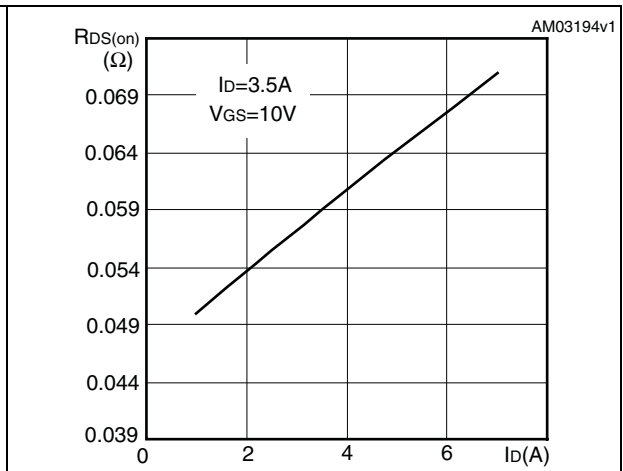


Figure 12. Gate charge vs gate-source voltage

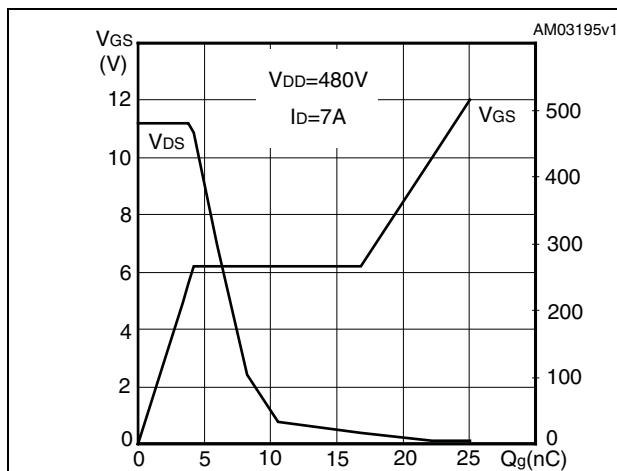


Figure 13. Capacitance variations

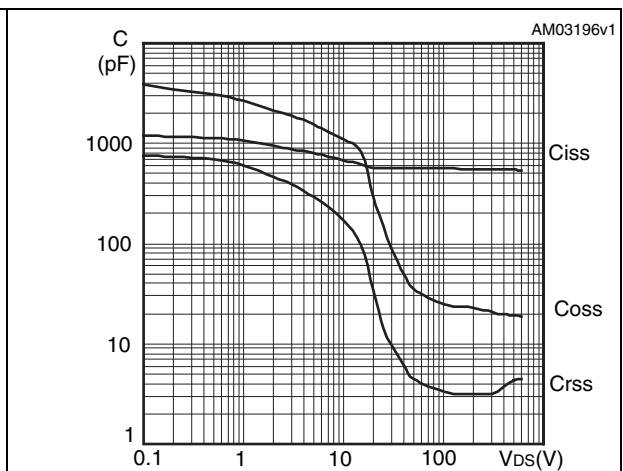


Figure 14. Normalized gate threshold voltage vs temperature

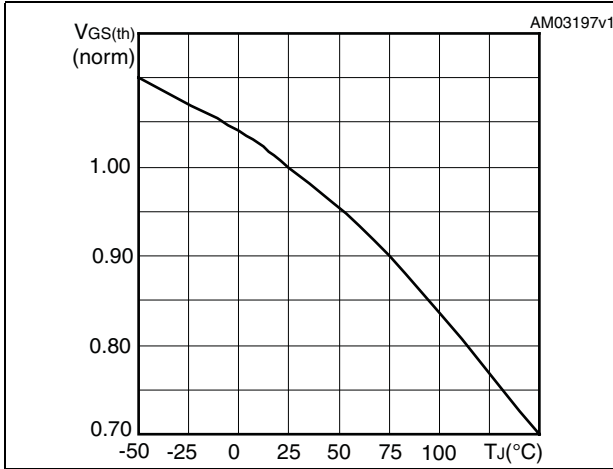


Figure 15. Normalized on resistance vs temperature

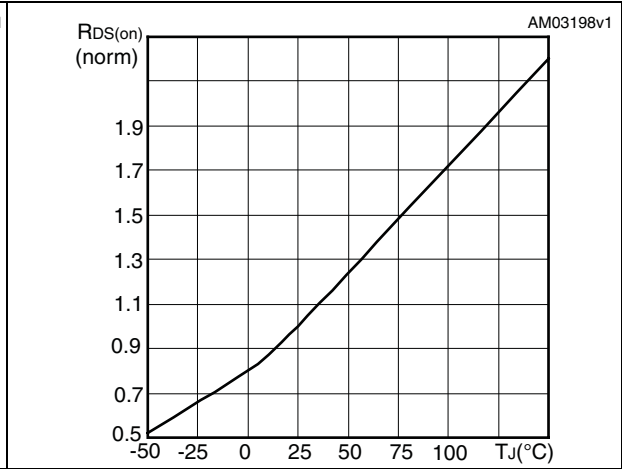


Figure 16. Source-drain diode forward characteristics

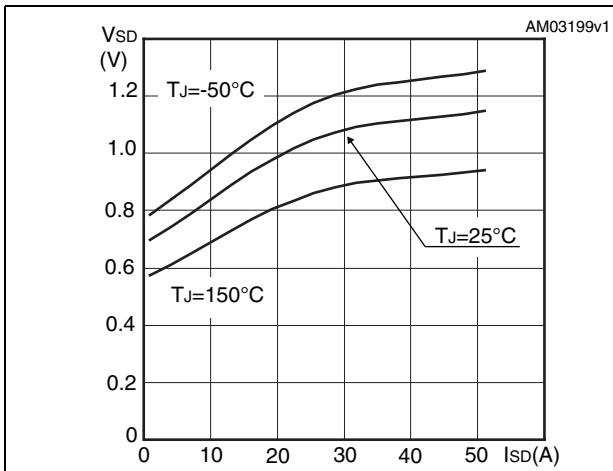
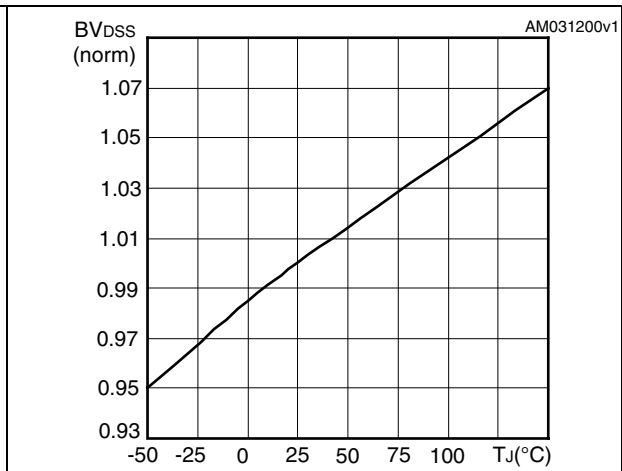


Figure 17. Normalized BV_{DSS} vs temperature



3 Test circuits

Figure 18. Switching times test circuit for resistive load

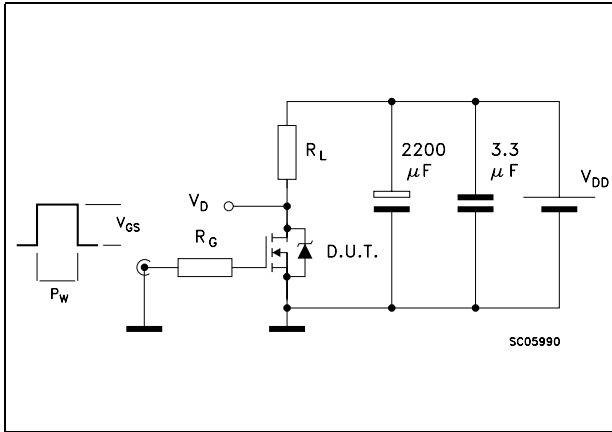


Figure 19. Gate charge test circuit

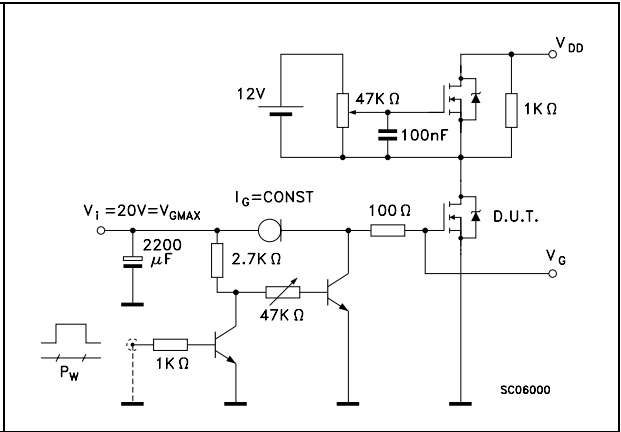


Figure 20. Test circuit for inductive load switching and diode recovery times

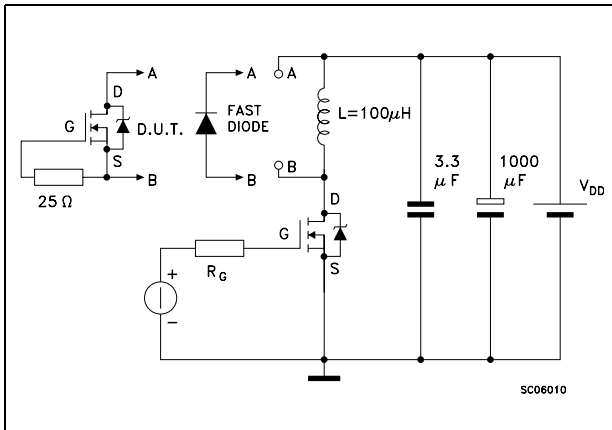


Figure 21. Unclamped inductive load test circuit

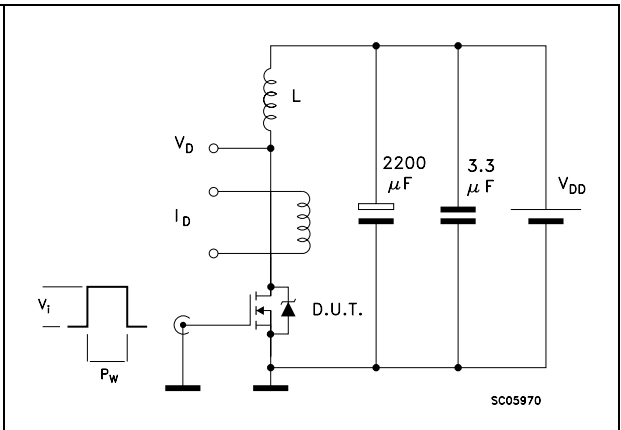


Figure 22. Unclamped inductive waveform

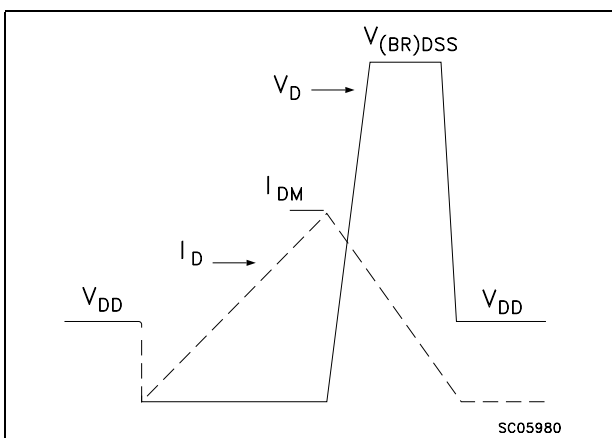
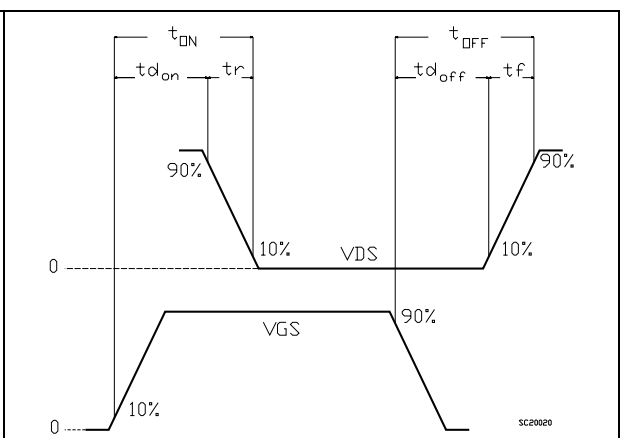


Figure 23. Switching time waveform

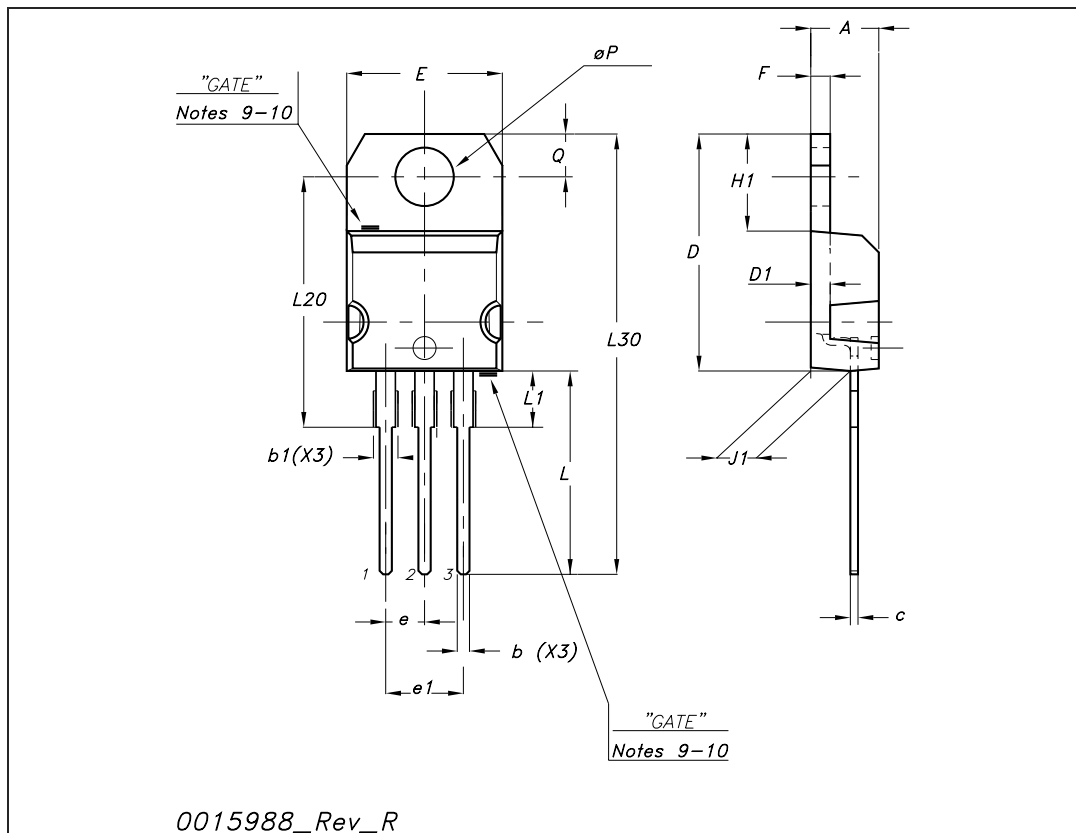


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

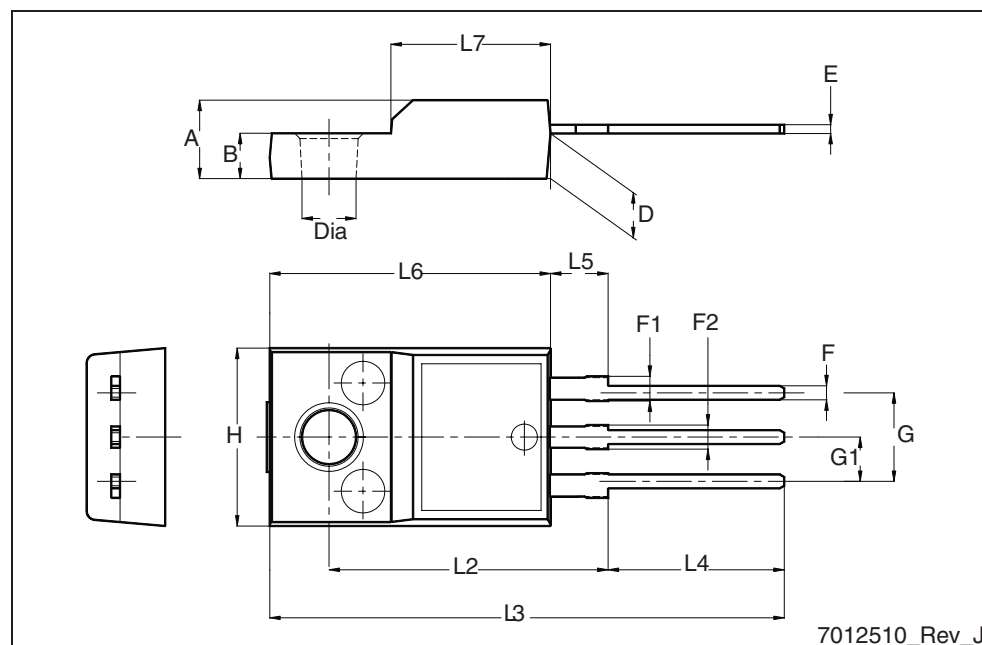
TO-220 mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.48		0.70	0.019		0.027
D	15.25		15.75	0.6		0.62
D1		1.27			0.050	
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.051
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
∅P	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



TO-220FP mechanical data

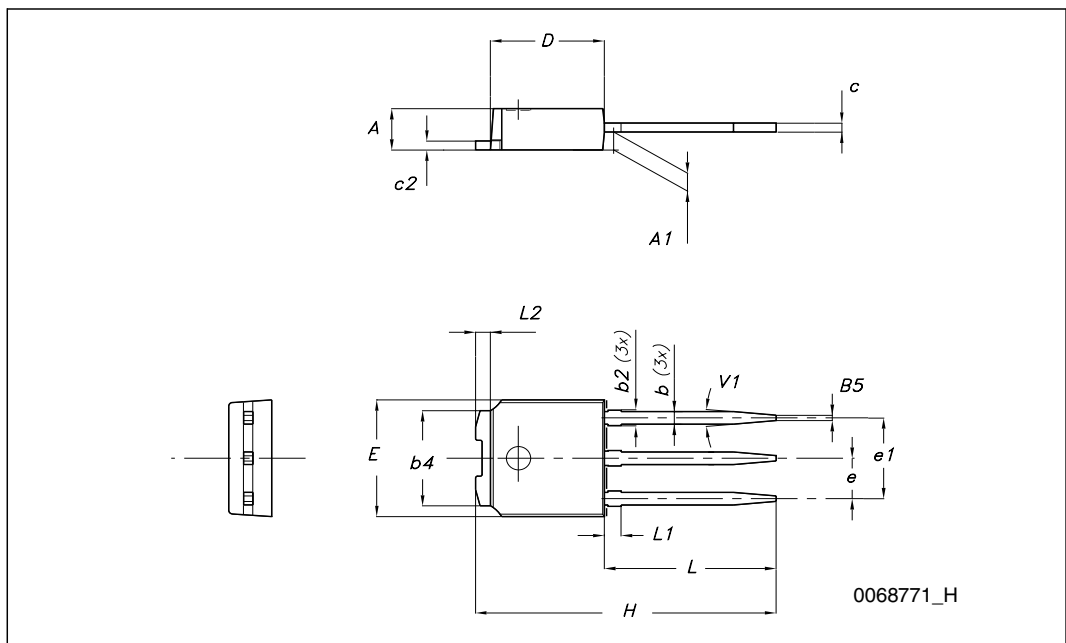
Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.5
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2



7012510_Rev_J

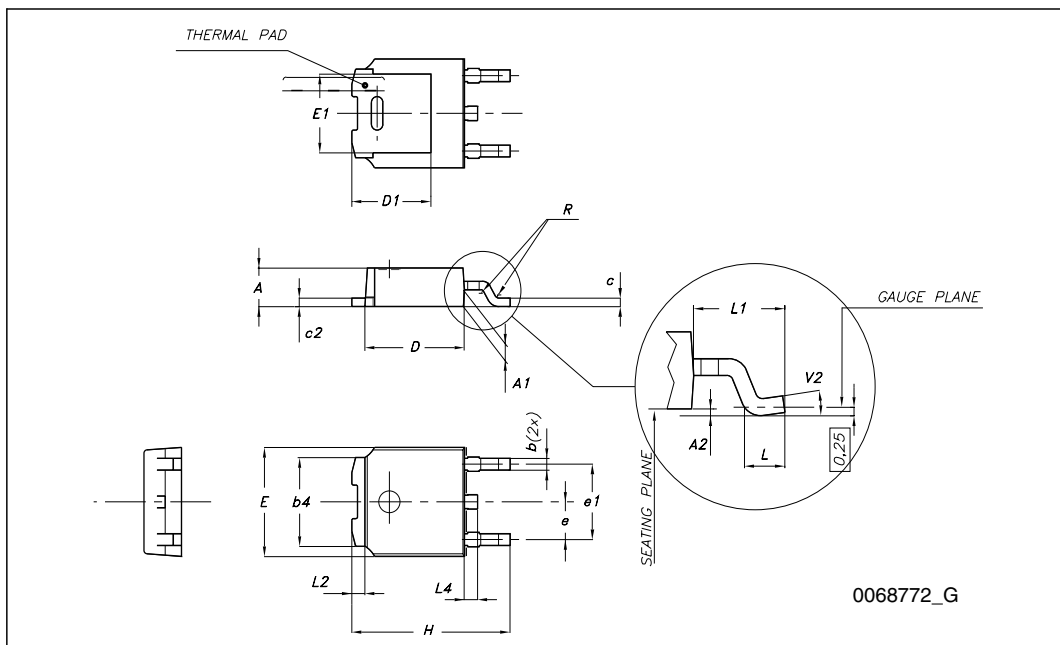
TO-251 (IPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	



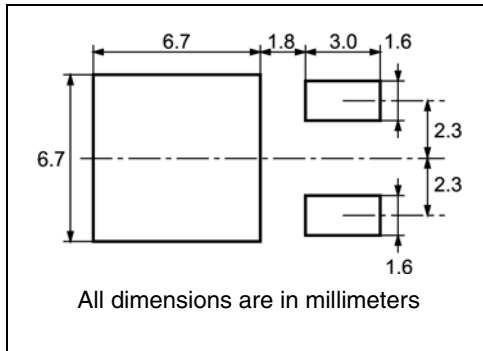
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



5 Packaging mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

TOP COVER TAPE

User Direction of Feed

Center line of cavity

Bending radius R min.

FEED DIRECTION

For machine ref. only including draft and radii concentric around B0

10 pitches cumulative tolerance on tape +/- 0.2 mm

6 Revision history

Table 9. Document revision history

Date	Revision	Changes
09-Feb-2009	1	First release

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2009 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com